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R. Walker

1050 U.S. PTO  
09/1955600  
09/19/01

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Rule 53(b) Divisional Application of:

Nobuhiko HAYASHI, et al.

Divisional of S.N.: 09/361,246 Filed July 27, 1999

Group Art Unit: To Be Assigned

Filed: Herewith

Examiner: To Be Assigned

For: SEMICONDUCTOR DEVICE AND METHOD OF FABRICATING THE SAME AND  
METHOD OF FORMING NITRIDE BASED SEMICONDUCTOR LAYER

**INFORMATION DISCLOSURE STATEMENT**  
**PURSUANT TO 37 CFR 1.97(b)**

Commissioner for Patents  
Washington, D.C. 20231

September 19, 2001

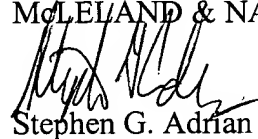
Sir:

This Information Disclosure Statement is being filed in order to comply with Applicant's duty of disclosure under 37 CFR 1.56. The documents listed on the Form PTO-1449 were made of record in parent application Serial No. 09/361,246 filed July 27, 1999.

The Commissioner is authorized to charge our Deposit Account No. 01-2340 for any fee which is deemed by the Patent and Trademark Office to be required to effect consideration of this statement.

Respectfully submitted,

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